KRAVCHENKO, A.A., kand.med.nauk

Therapeutic use of radicactive phosphorus in osteoplastic surgery; experimental studies. Ortop.travm. i protez. 20 no.6:79-83 Je '59.

[MIRA 13:3]

1. Iz Ukrainskogo nauchno-issledovatel skogo instituta ortopedii i travmatologii im. M.I. Sitenko (direktor - chlen-korrespondent AMN SSSR prof. N.P. Novachenko).

(PHOSPHORUS, radioactive,

eff. on bone regen. after exper. osteoplasty (Rus)) (BONE AND BONES, surg.

exper. osteoplasty, eff. of radiophsophorus on porop. bone regen. (Rus))

COLUMN TARGET CONTRACTOR CONTRACT

Clinical evaluation of osteoplastic operations in the treatment of recent and unknitted fractures of the long bones. Vest. khir. 83 no.7:62-69 Jl '59. (MIRA 12:11)

1. Iz Ukrainskogo nauchno-issledovatel'skogo instituta ortopedii i travmatologii im. prof.M.I.Sitenko (dir. - prof.N.P.Novachenko).

(BONE GRAFTING)

KRAVCHEKO, A.A., kand.med.nauk

Biological effect of radioactive phosphorus on the osteogenic capacity of an injured osseous organ. Trudy Ukr. nauch.-issl. inst. ortop. i travm. nc.15:347-354 '59. (Mira 16:12)

l. Iz Ukrainskogo nauchno-issledovatel skogo instituta ortopedii i travmatologii imeni prof. M.I.Sitenka (dir.-chlenkorrespondent AMN SSSR prof. N.P.Novachenko).

Tetovicus and the property of the property of

KRAVCHENKO, A. A.

Inhalation effect of the water of Hot Springs, No. 63 on blood pressure in hypertension. Sovet. med. no.8:32-34 Aug. 1950.

(CIMI 20:1)

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1. Of the Clinic for Mar, Throat, and Nose Diseases (Director -- Prof. V. K. Suprunov), Kuban' Medical Institute imeni Krasnaya Armiya.

APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R0008262300

KRAVCHENKO, A.A., starshiy nauchnyy sotrudnik

Metastases of ovarial tumor simulating thrombosis of the cavernous sinus. Vest.oto-rin. 18 no.5:115-116 S-0 '56. (MLRA 9:11)

1. Iz kliniki bolezney ukha, gorla i nosa Moskovskogo oblastnogo klinicheskogo instituta (dir. - prof. I.Ya. Sendul'skiy)
(OVARIES, neoplasms

metastases to cavernous sinus simulating thrombosis)

(VEINS, CRANIAL SINUSES, neoplasms

metastatic from ovaries in cavernous sinus simulating thrombosis)

(THROMBOSIS, differ. diag.

cavernous sinus therombosis simulated by metastatic tumor from ovaries)

KRAVCHENKO, A.A., starshiy nauchnyy sotrudnik

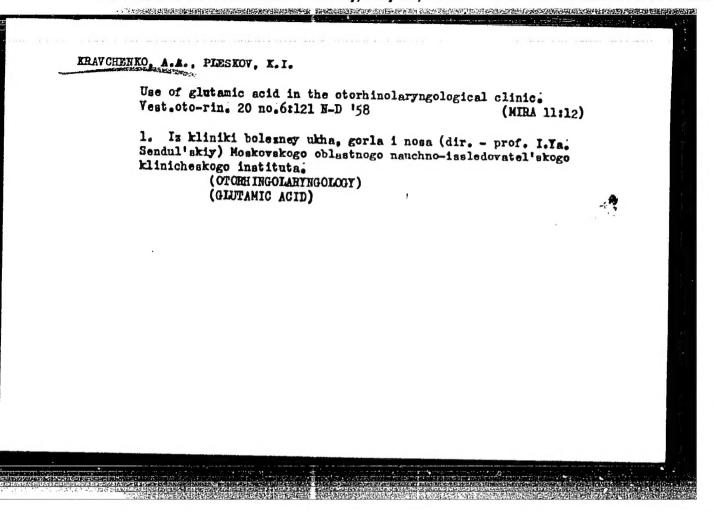
Exacerbation of chronic suppurative epitympanitis of the left ear in Addison's disease. Vest. oto-rin. 19 no.1:99-100 Ja-7 '57

(MIRA 10:4)

1. Is kliniki bolezney ukha, gorla i nosa (dir.-prof. I.Ya. Sandul'skiy) Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta.

(EAR, MIDDLE, diseases, epitympanitis, exacerbation in Addison's dis.) (Rus)

(ADDISON'S DISEASE, complications, epitympanitis, exacerbation) (Rus)



SVETLAKOV, M. I., dotsent, KRAVCHENKO, A.A., kand.med.nsuk, PLESKOV, K. I.

Use of hemopoietic stimulators in radiotherapy for cancer of the larynx. Vrach.delo no.5:527 My '58 (MIRA 11:7)

1. Klinika bolesney ukhs, gorla i nosa (zav. - prof. I.Ya. Sendul' skiy) Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta i Tsentral'nogo instituta usovershenstvovaniya vrachay.

(LARYEX--CAHCER)

(INUCOPRNIA)

(X RAYS--PHYSIOLOICAL FFFECT)

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SVETLAKOV, M.I., polkovník med.sluzhby, dots.; KRAVCHENKO, A.A., kand.med.

Nasal and pharyngeal hemorrhage requiring hospital therapy. Voen.-
med.zhur. no.12:60-62 D '58.
(MPISTAXIS, ther.
severe, in hosp. (Rus))
(PHARINX, hemorrh.
ther., in hosp. (Rus))
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SVETIAKOV, M.I., dots.; KHAVCHENKO, A.A., kand.med.nauk

Tympanoplasty in chronic suppurative otitis media. Vest.otorin.
20 no.2:20-23 Mr-Ap '58. (MIRA 12:11)

1. Iz kliniki bolezney ukha, gorla i nosa (zav. - prof.I.Ya.
Sendul'skly) Moskovskogo oblastnogo nauchno-issledovatel'skogo
klinicheskogo instituta i TSentral'nogo instituta usovershenstvovaniyu vrachey.

(OTITIS MEDIA, surg.

tympanoplasty in chronic suppurative dis.

(Hus))

SVETLAKOV, M.I.; KRAVCHENKO, A.A.; KARPUKHIN, V.I.

er er eine Bereichen der Bereichen der Bereichen der Bereichen der Bereichen Bereichen

Changes in arterial pressure in patients with laryngeal cancer in operations on the neck under potentiated local anesthesia. Akt. vop. obezbol. no.2:182-194 (59. (MIRA 14:5)

1. Iz kliniki bolezney ukha, gorla i nosa (zaveduyushchiy - prof. I.Ya.Sendul'skiy) Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta i TSentral'noy klinicheskoy bol'nitsy Ministerstva putey soobshcheyina (nauchnyy rukovoditel' - prof. T.P.Makarenko).

(BLOOD PRESSURE) (LARYNX -- CANCER)
(LOCAL ANESTHESIA)

Diseases of the upper respiratory tract and ears in workers at the Serpukhov textile mills. Gig. 1 san. 24 no.6:48-51 Jn '59. (MIRA 12:8)

1. Iz Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta imeni Vladinirskogo, Moskovskogo nauchno-issledovatel'skogo instituta sanitarii i glglyeny imeni F.F.Friemana i ob"yedinennoy bol'nitsy imeni Semashko Serpukhova. (OCCURATIONAL DISMASES ear & upper resp. tract dis. in textile workers (Rus)) (KAR, dis. occup., in textile workers (Rus)) (RESPIRATORY TRACT, dis. same)

KRAYCHENKO, A.A.; NEVRAYEVA, A.S.

Autonomic labyrinthine reactions in patients with hypertension treated by inhalation of artificial hydrogen sulfide water (outside of a health resort). Terap.arkh. 31 no.10:33-37 0 159.

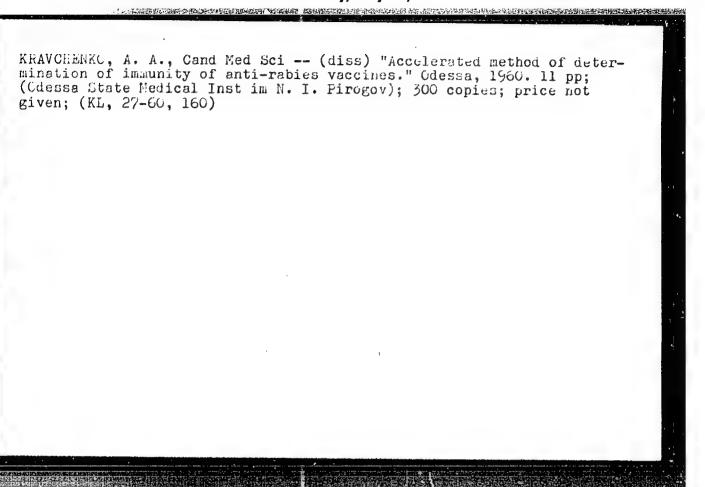
(MIRA 13:3)

1. Iz TSentral'nogo instituta kurortologii (direktor G.N. Pospelova)

i kliniki ushnykh, gorlovykh i nosovykh bolezney (direktor - prof.

I.Ya. Sendul'skiy) Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta imeni N.F. Viadimirskogo.

(MINERAL WATER, ther.)
(HYPERTENSION ther.)
(SULFIDES ther.)



KRAVCHERNO, A.A. (Monkva); PASTERNAK, A.Ye. (Monkva); NARYSHKHMA, T.F.

(Monkva); VOL'FSON, M.T. (Monkva)

Occupational pathology of the otolaryngological organs in workers of cotton mills. Gig. truda i prof. zab. 4, no.6:41-43 Je '60.

(MRA 15:4)

1. Monkovskiy oblastnoy klinicheskiy institut imeni M.F. Vladimirskop, Institut sanitarii i gigiyeny imeni F.F. Eriamana i Bol'nitsa fabriki "Krasnyy teksil'shchik".

(COTTON MANUFACTURE—HYGIENIC ASPECTS) (OTOLARYNGOLOGY)

MENAUGHENKO, A.A.; NEVERTEVA, A.S.

Influence of inhalations of artificial hydrogen sulfide wiater on the oscillographic indexes of hypertension patients, Vrach. delo no.7:117-119 Jl '60. (MIRA 13:7)

1. TSentral'nyy institut kurortologii i klinika ushnykh, gorlovykh i nosovykh bolesney Moskovskogo oblastnogo nauchno-iseledovatel'-skogo klinicheskogo instituta. (HYDROGEN SULFIDE) (HYPERTENSION)

KHAVCHENKO, A.A.; GORBACHEVA, K.M.; BOGOMOLOVA, Ye.R.; BITSADZE, L.R.

Change in the auditory function of the ear in treating hypertension with some medicinal substances (preliminary report). Vop. klin. pat. no.3:78-88 '61. (Mid 14:12)

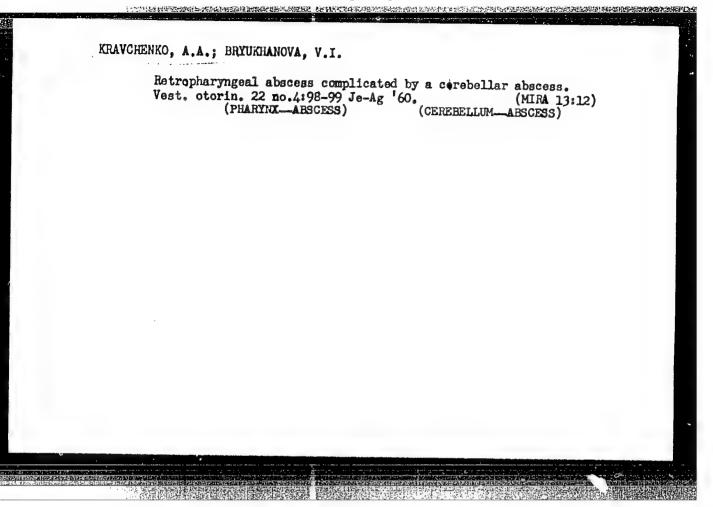
l. Iz Kliniki bolezhey ukho, gorla i nosa (zaveduyushchiy zasluzhennyy deyatel' nauki prof. I.Ya.Sendul'skiy) Moskovskogo oblastnogo nauchno-issledovatel'skogo instituta imeni M.V.Vladimirskogo.

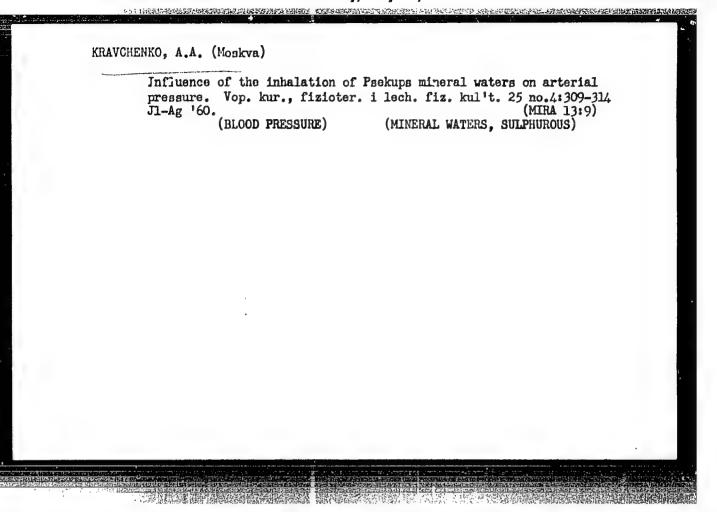
(HYPERTENSION) (HEARING)

KRAVCHENKO, A.A.; EOGOMOLOVA, Ye.R.; PLESKOV, K.I.; YUDIN, Yu.O.

Problem of clinical and morphological changes of the upper respiratory tract and ear in leukoses. Vest. otorin. 22 no. 4:33-38 Je-Ag '60. (MIRA 13:12)

(RESPIRATORY ORGANS) (EAR) (LEUKEMIA)





KRAVCHENKC, A.A.; NEVRAYEVA, A.S.

Condition of the auditory analysor in hypertension patients treated with vapor inhalations from hydrogen sulfide water. Vop. kur., fizioter. i lech. fiz. kul't. 26 no.5:420-426 3-0 '61. (MTR 14:11)

THE HOLLEGER HE SECTION FROM PROCESS OF THE REPORT OF THE SECTION OF THE PROCESS OF THE PROCESS

l. Iz TSentral nogo instituta kurortologii (dir. G.W.Pospelova) i kliniki ushnykh, gorlovykh i nosovykh bolezney (dir. - prof. I.Ya. Sendul'skiy), Moskovskogo oblastnogo klinicheskogo instituta (dir. P.M.Leonenko, rukovoditel' raboty-prof. Z.Ye.Bykhovskiy).

(HYPERTENSION) (MINERAL WATER, SULFUROUS)

(ACOUSTIC NERVE)

中心经验的现在 计图形表现存储器 医视频性反射 医多种生物 的复数医多种性神经

KRAVCHENKO, A.A., starshiy nauchnyy sotrudnik; MIRONOV, B.I.;

"HALASHOV, V.I.

Vestibulometry and exphemometry in hypertensives. Trudy (MIRA 16:4)

1. Otorinolaringologicheskaya klinika Moskovskogo oblastnogo nauchno-issledovatel skogo kliniches.ogo instituta (direktor - zasluzhennyy deyatel nauki, prof. I.Ya.Sendul skiy).

(HYPERTENSION) (VESTIBULAR APPARATUS)

(BLOOD—OXYGEN CONTENT)

THE NAME OF THE PERSON OF THE

KRAVCHENKO A.A. starshiy nauchnyy sotrudnik

Some data concerning the effect of sulfide mineral water on the brain blood vessels and the pressure of the cerebrospinal fluid. Trudy MONIKI no.5:142-159 *62. (MIRA 16:4)

1. Otorinolaringologicheskaya klinika Moskovskogo oblastnego nauchno-issledovatel'skogo klinicheskogo instituta imeni Vladimirskogo (dir. - zasluzhennyy deyatel' nauki, prof. I.Ya. Sendul'skiy) i laboratoriya eksperimental'noy patofiziologii mozga Instituta nevrologii AMN SSSR (zav. - chlen-korrespondent AMN SSSR B.N.Klosovskiy).

(MINERAL WATER, SULFUROUS) (BRAIN-BLOOD SUPPLY)
(CEREBROSPINAL FLUID)

KRAYCHENKO, A.A., starshiy nauchnyy sotrudnik Late results of treatment of hypertension patients with auditory and vestibular disorders by means of sulfide water inhalations. Trudy MUNIKI no.5:160-176 '62. (MIRA 16:4) 1. Klininka ushnykh, gorlovykh i nosovykh obezney Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta imeni Vladimirskogo (dir. - zasluzhermyy deyatel' nauki, prof. I.Ya.Sendul'skiy). (HYPERTENSION) (FAR-DISEASES) (INHALATION THERAFT)

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KRAVCHENKO, A.A. starshiy nauchnyy sotrudnik

State of the auditory analyser in hypertension patients treated by inhalation of natural sulfide water. Trudy MONIKI no.5:177-206 '62. (MIRÀ 1614)

1. Klinika ushnykh, gorlovykh i nosovykh bolezney Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta imeni Vladimirskogo (dir. - zasluzhennyy deyatel' mauki, prof. I.Ya.Sendul'skiy).

(HYPERTENSION) (EAR-DISEASES) (INHALATION THERAPY)

KRAVCHENKO, A.A.; BOGOMOLOVA, Ye.R.; PLESKOV, K.I.; YUDIN, Yu.G.

Glinical and morphological changes in the ear, nose and throat in reticulosis with a tumorlike growth. Vop. klin. pat. no.2:244-251 *61 (NIRA 16:12)

1. Iz kliniki bolezney ukha, gorla i nosa (zav. - sasluzhennyy deyatel' nauki prof. I.Ya. Sendul'skiy) i patomorfologicheskogo otdela (zav. - prof. S.B. Vaynberg [deceased]) Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta imeni Vladimirskogo.

ARUTYUNOV, V.Ya., prof.; KRAVCHENKO, A.A., doktor med. nauk; COINCKOVA, V.A., kand. med. nauk

Wegener's syndrome. Vest. derm. 1 ----. 37 no.5:30-35 My 163. (MERA 17:5)

1. Klinika kozhnyki i venerielezikh bolezney (dir. - pref. V.Ya. Arutyunov) otolaringologicheskaya klinika (dir. - zazluzhennyy deyatel' nauki prof. I.Ya. Sendul'skiy) i patomerfologicheskiy otdel (zav. - chlen-korrespondent AMN SSSk prof. 1.F. Avtsyn) Moskovskogo oblastnogo nauchno-issledovatel'sko o klinicheskogo instituta imeni M.F. Vladimirskogo (dir. - zasluzhennyy vrach P.M. Leonenko).

DOROFEYEV, V.G.; KITOV, A.N.; KRAVCHENKO, A.A., inzh., retsenzent;
HRAYLOVSKIY, N.G., inzh., red.; KHITROVA, N.A., tekhn.red.

[Servicing of passenger cars] Ekipirovka passazhirskikh
vagonov. Moskva, Izd-vo "Transport," 1964. 135 p.

(MIRA 17:3)

EWT(1)/EEC(b)-2/EAD-2 IJP(c)/AS(EP)-2/AFTC(b)/SSD/AFWIL/ASD(a)-5/ L 12021-65 5/0302/64/000/003/0062/0064 RAEM(c)/ESD(t) ACCESSION NR: AP4046115 B AUTHOR: Kravchenko, A. A. TITLE: Instrument for determining local values of magnetic field strength along the symmetry axis of magnetostatic lenses of an electron microscope SOURCE: Avtomatika i priborostroyeniye, no. 3, 1964, 62-64 TOPIC TAGS: electron microscope, magnetic field strength, magnetic field, magnetostatic lens ABSTRACT: The instrument consists of a Hall-generator-type sensor made from a Ge single crystal, a microammeter, and auxiliary switches and resistors. The sensor can be placed by a micrometer screw to any position on the magnetic lens axis. The instrument characteristics are: ranges, 0-100, 0-500, 0-1,000, 0-5,000, 0-10,000, 0-15,000 gs; basic error, \$2%; sensitivity, 40 microvolt/oe; sensor size, 2.5x2.5x0.3 mm. Orig. art. has: Z figures and 1 table.

Card 1/2

	L 12021-65 ACCESSION NR: ASSOCIATION: S	AP4046115	tata annu kiri	nikroskopov	(Sumy* Factor	y of
	ASSOCIATION: S Electron Microso	opes)	Intronut,			
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OVECHKIS, YE. S., KHAYCHENKO, A. D., GRAD, N. YE. IRLINOKIY, D. A., TSIFENYUK, A. YA.

Hides and Skins

Efficient method for measuring stiff hides. Leg. prom. 12 no. 8, 1952.

Fonthly List of Russian Accessions. Library of Congress, October 1952. UNCLASSIFIED.

Semiautomatic machines for shaping and assembling shoes having sewed and glued seles. Izv. vys. ucheb.zav.; tekh.leg. prom. no.1:57-66 '58. (MIRA 11:6)

1.Ukrainskiy nauchne-issledovatel'skiy institut kozhevenne-obuvnoy promyshlennesti. (Shee machinery)

APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R0008262300

Wraychenko, A.D., inzh.

Using the method of two-dimensional stretching in investigating physical and mechanical properties of chrome-tanned calf leather.

Izv.ys.ucheb.zav.; tekh.leg.prom. no.4:45-58 '58. (MIRA 11:12)

1.Ukrainskiy nauchno-issledovatel'skiy institut kozhevenno-obuvnoy promyshlennosti.

(Leather--Testing)

KRAYCHENKO, A.D., inzh.

Investigating physicomechanical properties of chrome-tanned calfskin by two-dimensional stretching. Izv.vys.ucheb.zav.; tekh.leg.prom. no.5:35-46 '58. (MIRA 12:2)

1. Ukrainskiy nauchno-issledovatel'skiy institut kozhevenno-obuvnoy promyshlennisti. (Leather--Testing)

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KRAVCHENKO, A.D., inzh.; Prinimala uchastiye: ROKHLENKO, R.

为15年的19年1月1日,19年1日,19年1日,19年1日,19年1日,19年1日,19年1日,19年1日,19年1日,19年1日,19年1日,19年1日,19年1日,19年1日,19年1日,19年1日,19年1日,1

Studying the effect of moisture on the deformation of shoe upper materials in cases of two-dimensional stretching. Izv.vys.ucheb. zav.; tekh.leg.prom. no.6:84-91 '61. (MIRA 14:12)

1. Ukrainskiy nauchno-isaledovatel skiy institut kozhevenno-obuvnoy promyshlennosti. Rekomendovana kafedroy tekhnologii obuvnogo proizvodstva Kiyevskogo tekhnologicheskogo instituta legkoy promyshlennosti.

(Shoe manufacture) (Strains and stresses)

KRAVCHENKO, A.D., inzh.

Investigating the deformation of shoe uppers and their fastening to the sole parts on a semiautomatic multiple-operation line for the forming and assembly of welt footwear. Nauch.-issl.trudy Ukr NIIKP no.13:117-131 '62. (MIRA 18:2)

26.2421

26028

S/.39/61/000/003/008/013 E036/E335

AUTHOR:

Kravchenko, A.F.

TITLE:

Some Electrophysical Properties of Gallium

Arsenide

PERIODICAL: Izvestiya vysshikh uchebnykh zavedeniy,

Fizika, 1961, No. 3, pp. 80-87

TEXT: An account is given of the investigation of the temperature dependence of the electrical conductivity, thermo-electric e.m.f. and the Fermi level in gallium arsenide of both conductivity types. The effective masses and concentrations of electrons and holes and the variation of the Hall coefficient with both temperature and magnetic field were determined and thus also the temperature dependence of the mobility. These experimental results are compared with theoretical calculations and some comments are made on the carrier scattering mechanism. The author states that insufficient work of this sort has been carried out to make possible some conclusions on the energy structure or conduction mechanism of gallium arsenide. Rectangular parallelopiped Card 1/6

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Some Electrophysical Properties ... E036/E335

samples were cut from polycrystalline ingots, the surface was then ground and the surface layer, which was deformed by cutting and grinding, removed by etching. Then, narrow strips of silver were deposited on the sides of the samples and tungsten probes pressed onto these for the Hall measurements and for the conductivity determination by a compensation method. Direct current was used for the Hall measurements. The usual compensation technique was used to measure the thermo-electric e.m.f. to an accuracy of \pm 1 $_{\mu}V$. The temperature difference along the sample of 10 \pm 15 $^{\circ}C$ was measured with two copperconstantan thermocouples. The differential thermo-e.m.f. was measured with respect to the copper branch of the thermocouple. In some cases the samples cut comprised a single crystal and no significant difference was observed between these samples and those containing two or three crystals. The measured thermoelectrical e.m.f. are of the order 0.03 - 0.05 mV/deg for n-type and 0.1 - 0.2 mV/deg for p-type material at room temperature. These values increase for both types with increasing temperature. Measurements are plotted over the range 300 K to approximately 600° K. The conductivity of n-type material increases slowly Card 2/6

26028 S/139/61/000/003/008/013 Some Electrophysical Properties E036/E335

with temperature to reach a maximum at $423~^{\circ}\mathrm{K}$ and then decreases. At about $473~^{\circ}\mathrm{K}$ the conductivity again sharply increases. In some n-type samples the conductivity is almost independent of temperature up to $473\,^{\circ}\mathrm{K}$ and then slowly increases. The conductivity of p-type material increases from room temperature somewhat more rapidly than that of natype. The Hall constant of n-type is independent of temperature from low temperatures up to ~ 200 K. A slight decrease of the Hall constant is observed for p-type material over this range. This change is stated to be less than that reported by Folberth and Weiss (Ref. 4 - Z. Baturforsch, 10a, 615, 1955). Over this range the conductivity of both no and p-type samples increased. The variation of the Hall constant with the magnetic field was measured at room temperature. For n-type samples a slight linear decrease with the field was observed. The decrease was smaller for the larger carrier concentrations and in one case was independent of the field over the range 80 to 20 000 Oe. The Hall constant of p-type samples drops sharply as the field is increased from 80 to $4\,\,000$ Oe. From $6\,\,000$ Oe it is practically constant. After this investigation all Hall Card 3/6

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26028 S/139/61/000/003/008/013 Some Electrophysical Properties E036/E335

measurements were carried out above 6 000 0e. The temperature dependence of the carrier mobility calculated from these Hall and conductivity measurements showed an increase from room temperature to a maximum at 400 - 420 K for n-type and at about 500 oK for patype. The typical mobilities were about $200 = 300 \text{ cm}^2/\text{Vsec}$ and 1 $400 = 1.600 \text{ cm}^2/\text{Vsec}$ for p= and n= type samples, respectively. The author states that measurements of the Nernst-Ettingshausen effect on these samples indicated that at lower temperatures scattering by impurities was dominant. This work is to be discussed in a separate paper. The decrease of mobility at the higher temperature and the slight dependence of the Hall constant on temperature suggests that the samples are degenerate. Variations of the Hall constant of Ge and InSb with magnetic field similar to those reported here have been explained by the presence of light and heavy holes and this may be the explanation in the case of gallium arsenide. The position of the Fermi level is calculated from the thermo-electric e.m.f. and supports the conclusions that the samples are degenerate. Card 4/6

26028 5/139/61/000/003/008/013 E036/E335 Some Electrophysical Properties ...

The carrier concentrations at room temperatures are calculated from Hall data to be $\sim 4.5 \times 10^{17} \text{cm}^{-3}$ for n-type and $\sim 7.8 \times 10^{17} \text{cm}^{-3}$ for p-type and the variation with temperature tallies with the degeneracy. The effective masses calculated from the data are $0.024~m_\odot$ for electrons and $0.093~m_\odot$ for holes, where m_\odot is the free electron mass. The observed thermo-electric e.m.f.'s are somewhat less than those calculated on the basis of one carrier type and may be due to the presence of carriers of both signs. Summarising, the increasing natype conductivity is consistent with impurity scattering, whilst with p-type the number of carriers also increases. The decrease in mobility at higher temperatures is due to thermal scattering. The fact that the maximum conductivity is observed at a higher temperature in p-type than in n-type is explained by the higher carrier concentration in p-type samples. The abrupt increase of netype conductivity at high temperatures could be due to deep impurity levels. The author expresses his gratitude to Card 5/6

26028 \$/139/61/000/003/008/013

Some Electrophysical Properties ... E036/E335

V.A. Presnov for the samples and to A.F. Gorodetskiy for interest in the work. There are 9 figures and 13 references: 6 Soviet and 7 non-Soviet. The four English language references quoted are: Ref. 2 - H. Welker - J. Electronics, 1, 181, 1955; Ref. 3 - R. Barrie, F. Cunnell J. Edmond, J. Ross - Physica, 20, 11, 1087-1090, 1954, Ref. 11 - R. Willardson, T. Harman, A. Beer - Phys. Rev., 96, 1512, 1954; Ref. 12 - J. Tauc - Phys. Rev., 95, 1394, 1954.

ASSOCIATION: Novosibirskiy elektrotekhnicheskiy institut

(Novosibirsk Electrotechnical Institute)

SUBMITTED: May 9, 1960 (initially)

November 26, 1960 (after revision)

Card 6/6

KRAVCHENKO, A.F.; FEN, G.Yu.

Galvanomagnetic and thermomagnetic phenomina in n-type Gals.
Fig. two. tela i.no.2:660-666 F 163. (MIRA 16:5)

1. Movosibirskiy elektrotekhnicheskiy institut.
(Thermomagnetism) (Thermoelectricity) (Gallium arsenide)

L 35490-65 ENT(1)/ENT(m)/ENP(w)/ENA(d)/T/ENP(+)/ENP(5)/ENA(h) Pz-6/Peb ACCESSION NR: AP5007839 : (c) JD/RT 5/0288/64/000/003/0091/0095

AUTHOR: Kravchenko, A. F.; Kot, K. N.; Divak, M. I.

TITLE: Microhardness of gallium arsenide

SOURCE: AN SSSR. Sibirskoye otdeleniye. Izvestiya. Seriya tekhnicheskikh nauk, no. 3, 1964, 91-95

TOPIC TAGS: gallium arsenide, gallium arsenide hardness, single crystal hardness, microscope hardness, semiconductor hardness, semiconductor crystal structure

ABSTRACT: Only a few papers deal with the microstructure of GaAs (see e.g., G.A. Wolff, L. Toman, F.I. Field, J.C. Clavk, Somiconductors and Phosphors, New Jersey, 1958 for polycrystalline samples). The present paper reports on measurements of the microhardness of oriented monocrystals having a free electron concentration of n 1017 cm 3, and a dislocation density in the [111] plane between 2:104 and 5:105 cm 2. Samples were polished by etching (1 part HF, 3 parts HNO₃, and 2 parts H₂). The microhardness in the [111] plane is H = 650 kg/mm²; in [110] - 510 kg/mm². Annealing at temperatures not higher than 400C increases the microhardness, which also depends on the orientation of the indenter with respect to the crystallographic directions

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ond is determi	ned by the distri	bution and mobilities and the heat of f	y of dislocations.	There is a proport V. The viscosity of art. has: 2 formu	ion- the las.
samples with 5 figures, and	in the fifth plan	18 th cdutt to a.			
ARGOCIATION	: Institut fiziki f	verdogo tela i poli	uprovodníkovoy _v e	ektroniki (Institute	for
Solid State Ph	yeics and Semico		CB)		
SUBMITTED:	10Jan64	ENCL: 00	SUB CODE: 8	S, EC	
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中国的政治和自己的思想的关系是自己的政治的影响是是影响。 法国现代的过程证明的法律证明的法律证明 Pt-10 IJP(c)/AFML/SSD/ ENT(1)/EPA(s)-2/ENT(m)/ENP(t)/ENP(b) AS(mp)-2/ASD(a)-5/RAEM(a)/ESD(gs)/ESD(t) JD s/0139/64/000/005/0062/0068 ACCESSION NR: AP4047349 AUTHOR: Kraychenko, A. F. Magnetoresistance in n-type gallium arsenide TITLE: IVUZ. Fizika, no. 5, 1964, SOURCE: TOPIC TAGS: gallium arsenide, magnetoresistance, galvanomagnetic effect, conduction band, carrier density, Hall effect ABSTRACT: The purpose of this investigation was to study further the structure of the conduction band in n-type GaAs and to obtain additional information concerning the location and form of the additional minima of the conduction band (in excess of those in germani-The tests were made over a wide interval of temperatures and concentrations, and in different crystallographic directions. The samples were in the form of right parallelepipeds 0.1 x 0.3 x 1.0 Much attention was paid to the surface finish and to the quality Card

L 11967-65

ACCESSION NR: AP4047349

of the current contacts. The temperature range was 4.2--300K, and the free-garrier density, calculated from the Hall effect, was 104 cm⁻³--10¹⁸ cm⁻³ at room temperature. The results have shown that the constant-energy surface is anisotropic in K-space for samples with carrier density ≤107 cm⁻³. There is practically no anisotropy when the impurity content is high. The coefficients of the magnetoresistance tensor were calculated for samples with different impurity concentration and different temperatures. The relation between these coefficients shows that the conduction of these samples lies in the lowest conduction band which has many minima distributed along the [100] axis. In these minima, the equal-energy surfaces are ellipsoids of revolution with major axes along the [100] direction. anisotropy exponent of the minima on [100] is close to the analogous minima for silicon. At liquid helium temperature, a negative magneto-resistance is observed for samples with density $n \sim 10^{17}$ cm⁻³ this magnetoresistance is isotropic. Several hypotheses are advanced concerning the structure of the conduction bands of GaAs.

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Unit for measuring the lifetime of minority charge carriers in semiconductors, 7sv. lab. 31 no.1: 26-127 '65.

(MIRA 18:3)

1. Novosibirskiy elektrotekhnicheskiy institut.

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EWT(m)/EWP(w)/EPF(c)/EWP(j)/T/EWP(t)/EWP(b) IJP(c) JD/RM L 2551-66 ACCESSION NR: AP5021083 UR/0288/65/000/002/0153 537.311.33 AUTHOR: Kornilovich, A. A.; Kravchenko, A. F. TITLE: Effect of heat treatment on the electrical properties of silicon containing phosphorus as an impurity SOURCE: AN SSSR. Sibirskoye otdeleniye. Izvestiya. Seriya tekhnicheskikh nauk, no. 2, 1965, 153-154 TOPIC TAGS: high temperature annealing, low temperature annealing, Hall effect, silicon, phosphorus impurity, free electron mobility, donor concentration, electrical resistance, electroneutral silicon dioxide ABSTRACT: Heating of Si to temperatures above 3500 markedly changes its electrical properties; the reason for this is mot conclusively known, although certain theories on the interaction of oxygen with atoms of silicon and atoms of impurities have been advanced. In this connection, the authors present the results of an experimental investigation of electrical resistance, concentration, and free electron mobility as a function of the time and temperature of the heat treatment (annealing) of three groups of n-Si containing different amounts of P impurity. The annealing was performed in a vacuum (10-3 mm Hg) at from 400 to 11000 for 30 min to 40 hr, and the cooling, for 10 hr, inside the furnace. The effect of annealing differed

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depending on the temperature range in which it was performed: above 800C the Hall coefficient and free-electron mobility tended to increase (most sharply in the material with the lowest content of P), while electrical resistance remained constant; below 800C (low-temperature annealing) the Hall coefficient and the electrical resistance of Si decreased while electron mobility somewhat increased. Annealing beyond 30 min no longer affected the electrical characteristics and parameters of Si. The differences in the effect of heat treatment on electrical properties are conditioned by the presence of oxygen in silicon in the form of monodisperse Si ₂ O groups. In the process of the heating of Si to 1000C the oxygen atoms	
become regrouped 8120 → 8102 + 81	
The electrically neutral groups of SiO2 interact with the phosphorus	
$58i\phi_2 + 4P + 2P_2O_5 + 58i$	
The resulting oxides of the impurity react with SiO2	
$/ xP_2O_5 + y81O_2 - P_x81_yO_2$	
As a result, the P and O atoms are bound into dischrically neutral PxSivO2 groups and the	
Card 2/3	

"APPROVED FOR RELEASE: Monday, July 31, 2000

CIA-RDP86-00513R000826230

ACCESSION NR: AP5021083 donor concentration decreases. On heating to 1300c the molecules of phosphorus- silica glasses, the oxides of the impurity, and the silicon dioxides decay, and the liberated oxygen diffuses through the interstices and, following rapid cooling of the crystal, is distributed in the form of Si ₂ O groups. By contrast, low-temperature treatment leads to the formation of electrically active SiO ₄ complexes from Si ₂ O groups. These complexes may be singly or multiply ionized, thus leading to an in- crease in free-electron concentration. The increase in electron mobility is clearly attributable to the decrease in the number of thermal defects in the process of pro- longed annealing. Orig. art. has: 3 figures. ASSOCIATION: Institut fiziki poluprovodnikov Sibirskogo otdeleniya AN SSSR, Novo- sibirsk (Institute of Semiconductor Physics, Siberian Department, AN SSSR) SUBMITTED: O8Oct64 ENCL: OO SUB CODE: MM, EM NO REF SOV: OOO OTHER: OO9 ATD PRESS: 4/10 9 Card 3/3 Card 3/3				
donor concentration decreases. On heating to 1300c the molecules of phosphorus- silica glasses, the oxides of the impurity, and the silicon dioxides decay, and the liberated oxygen diffuses through the interstices and, following rapid cooling of the crystal, is distributed in the form of Si ₂ O groups. By contrast, low-temperature treatment leads to the formation of electrically active SiO ₄ complexes from Si ₂ O groups. These complexes may be singly or multiply ionized, thus leading to an in- crease in free-electron concentration. The increase in electron mobility is clearly attributable to the decrease in the number of thermal defects in the process of pro- longed annealing. Orig. art. has: 3 figures. ASSOCIATION: Institut fiziki poluprovodnikov Sibirskogo otdeleniya AN SSSR, Novo- sibirsk (Institute of Semiconductor Physics, Siberian Department, AN SSSR) SUBMITTED: 080ct64 ENCL: 00 SUB CODE: MM, EM	L 2551-66	The same of the sa		
silica glasses, the oxides of the impurity, and the silicon dioxides decay, and the liberated oxygen diffuses through the interstices and, following rapid cooling of the crystal, is distributed in the form of Si ₂ O groups. By contrast, low-temperature treatment leads to the formation of electrically active SiO ₄ complexes/from Si ₂ O groups. These complexes may be singly or multiply ionized, thus leading to an increase in free-electron concentration. The increase in electron mobility is clearly attributable to the decrease in the number of thermal defects in the process of prolonged annealing. Orig. art. has: 3 figures. ASSOCIATION: Institut fiziki poluprovodnikov Sibirskogo otdeleniya AN SSSR, Novosibirsk (Institute of Semiconductor Physics, Siberian Department, AN SSSR) SUBMITTED: O8Oct64 ENCL: OO SUB CODE: MM, EM	ACCESSION NR: AP502108	83	- 2	
ASSOCIATION: Institut fiziki poluprovodnikov Sibirskogo otdeleniya AN SSSR, Novo- sibirsk (Institute of Semiconductor Physics, Siberian Department, AN SSSR) SUBMITTED: 080ct64 ENCL: 00 SUB CODE: MM, EM	silica glasses, the oxiditerated oxygen diffuse the crystal, is distributeratment leads to the i groups. These complexes crease in free-electron attributable to the decr	des of the impurity, and the es through the interstices a uted in the form of Si ₂ O groformation of electrically ac may be singly or multiply concentration. The increase in the number of them	e silicon dioxides decay, and the and, following rapid cooling of cups. By contrast, low-temperaturities 8104 complexes/from 8120 ionized, thus leading to an insec in electron mobility is clearly	re
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L 14562-66 ENT(m)/EMP(w)/T/EMP(t)/SIP(b) IJP(c) JD

ACC NR. APG002015 A SOURCE CODE: UR/0288/65/000/003/0079/0085

AUTHOR: Kravchenko, A. F.; Kornilovich, A. A.; Saks, L. A.; Sirotkina, V. P.

ORG: Institute of Semiconductor Physics, Siberian Branch, AN SSSR, Novosibirsk (Institut fiziki poluprovodnikov Sibirskogo otdeleniya AN SSSR)

TITLE: Electrical properties of silicon with phosphorus admixtures

在企业的企业中的企业的企业的企业的企业的企业的企业的企业的企业。1914年,1914年的企业的企业的企业的企业的企业的企业的企业的企业的企业的企业的企业的企业企业。

SOURCE: AN SSSR. Sibirskoye otdeleniye. Izvestiya. Seriya tekhnicheskikh nauk, no. 3, 1965, 79-85

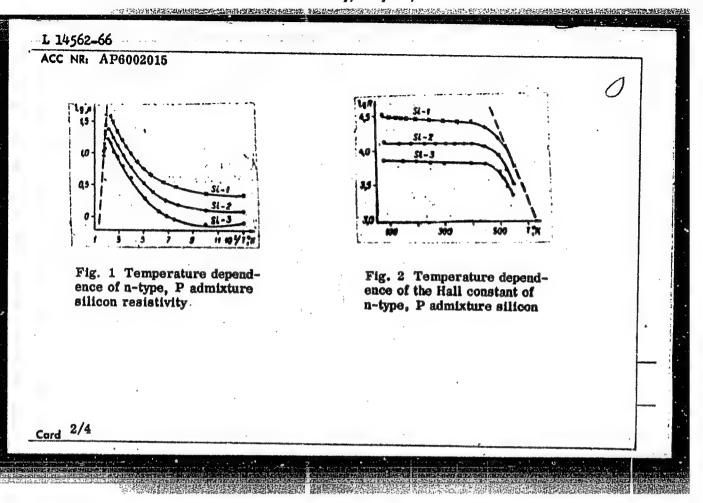
TOPIC TAGS: silicon semiconductor, specific resistance, Hall effect, thermoelectromotive force, phonon scattering

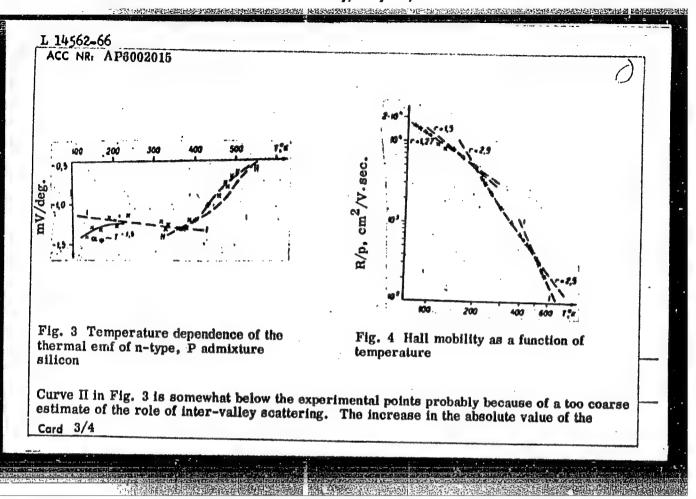
ABSTRACT: The majority of Carlier works concerning the influence of phosphorus on the physical properties of silicon were carried out on polycrystalline materials in which the intercrystalline potential barriers and the interpretation of kinetic effects extremely complicated. In view of the present-day uses of n-type silicons with low P content, the authors investigated effects in three types of Si samples (Si-1, Si-2, Si-3) with differing P concentration having at room temperature specific resistivities of 18, 9, and 6 ohm cm. Experimental results are summarized in Figures 1 through 4. A detailed theoretical interpretation of the experimental results is also given. The theoretical dashed curves in Fig. 4 are in good agreement with experimental data except in the low temperature region, where the deviation may be due to admixture scattering which was neglected during the theoretical derivation.

UDC: 539.293:538.632

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varca)/aar(t)/sig Idi (c) 1:/50 ACC NA Abs. 156.15 SOURCE CODE: UR/0139/66/000/003/0074/0079 AUTHOR: Kravehenko, A. F. ORG: Institute of Physics of Semiconductors, SO AN SSSR (Institut fiziki poluprovod-TITLE: Galvanomagnetic and thermomagnetic phenomena in compensated gallium arsenide SCURCE: IVUZ. Fizika, no. 3, 1966, 74-79 TOPIC TAGS: gallium arsenide, galvanomagnetic effect, thermomagnetic effect, Hall effect, magnetoresistance, Nernst effect, Ettingshausen effect, electron density, electron mobility, electron scattering APSTRACT: The author measured, in a wide range of temperatures, several kinetic characteristics of gallium arsenide (Hall effect, magnetoresistance, Nernst-Ettingshausen effect) in which the free-e extron density at room temperature did not exceed 1015. em-3. The purpose of the invertigation was to determine the dominating mechanism of scattering and to explain the previously observed disparity between the electron mobility and the electron density. Standard procedures were used for the measurements. The results show that at low temperatures the electrons are scattered predominantly from the impurity atoms and from the optical vibrations, while at high temperatures the scattering is by acoustic phonons. In the presence of simultaneous scattering by thermal vibrations and by impurity ions, the principal role in the longitudinal Nernst Ettingshausen effect at T > 300K is played by the scattering by acoustic phonons. 1/2 Card

ACC NR: ANO23415

Whereas the transverse Nernst-Ettingshausen effect reverses sign near 285%, the longitudinal one does not. The mobility calculated from the dependence of the magnetoresistance on the magnetic field intensity does not agree with the value of the mobility measured from the Hall effect. The discrepancy is attributed to a possible anisotropy of the scattering. Orig. art. has: 3 figures and 4 formulas.

SUB CODE: 20/ SUBM DATE: 31Aug64/ ORIG REF: 006/ OTH REF: 014

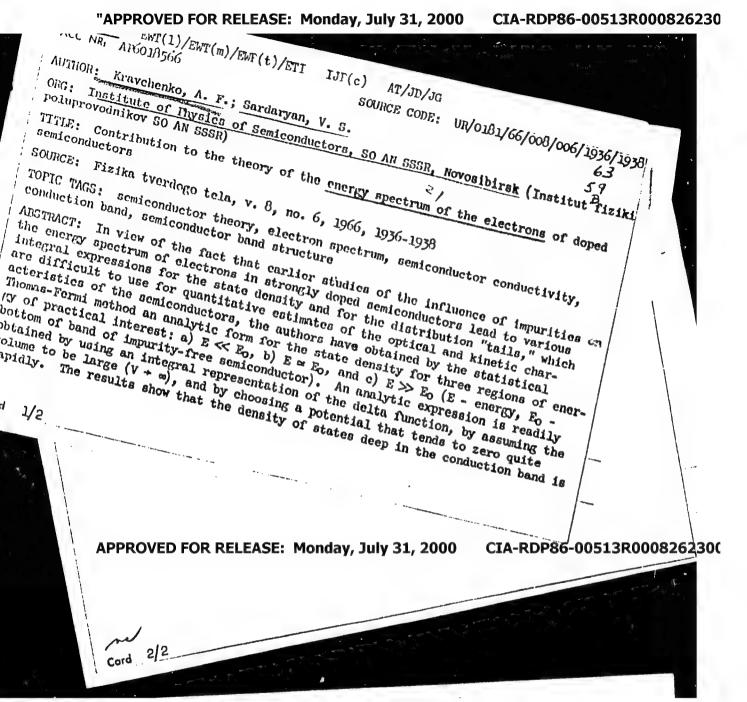
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L 38890-66 EWT(1) IJP(c)
ACC NR: AP6018557 SOURCE CODE: UR/0181/66/008/006/1899/1902
AUTHOR: Kravchenko, A. F.; Sardaryan, V. S.; Magarill, L. I.
ORG: Institute of Physics of Semiconductors, SO AN SSSR, Novosibirsk (Institut fiziki poluprovodnikov SO AN SSSR)
TITLE: On the phenomenological theory of the longitudinal Hall effect
SOURCE: Fizika tverdogo tela, v. 8, no. 6, 1966, 1899-1902
TOPIC TAGS: Hall effect, cubic crystal, semiconductor conductivity
AESTRACT: A phenomenological theory is developed for the longitudinal Hall effect in cubic crystals in the case of anisotropic relaxation time and two-band conductivity, and anisotropic dispersion. Expressions are derived for the different components of the conductivity corresponding to both spherical and anisotropic minima, neglecting intervalley transitions. Formulas are then presented for the coefficients of the generalized conductivity tensor in terms of experimentally measured quantities. In the latter case expressions are given for both the longitudinal and planar Hall effects. The results show that the longitudinal Hall field does not act on the spherical minimum, whereas the planar and ordinary Hall fields are expressed in terms of kinetic parameters of both bands, and that experimental investigation of the longitudinal Hall effect yields important information on the anisotropy of the additional minima. The authors thank V. L. Pokrovskiy for valuable remarks. Orig. art. has: 23 formulas.
SUB CODE: 20/ SUBM DATE: O2Aug65/ ORIG REF: OO4/ OTH REF: OO4
Card 1/1/114
L 10074-66

APPROVED FOR RELEASE: Monday, July 31, 2000

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L 06230-67 EWT(1)/EWT(m)/EWP(t)/ETI/EWP(k) LJP(c) JD/JG SOURCE CODE: UR/0046/66/012/003/0369/0372 4/

AUTHOR: Bobylev, B. A.; Kravchenko, A. F.

ORG: Institute of the Physics of Semiconductors, SO AN SSSR, Novosibirsk (Institut fiziki

poluprovodnikov, SO AN SSSR)
TITLE: Absorption of ultrasonic waves in junctions of GaAs and GaSb

SOURCE: Akusticheskiy zhurnal, v. 12, no. 3, 1966, 369-372

TOPIC TAGS: ultrasonic wave, phonon interaction, ultrasound absorption

ABSTRACT: This paper presents experimental measurements of the damping of ultrasonic waves in semiconductor junctions of GaAs and GaSb. The frequency dependence of this absorption is examined in the range 20-200 megacycles; the temperature dependence is observed over the interval $T = 95^{\circ}$ K to $T = 300^{\circ}$ K. The measurements were made using the "pulse technique" in which radiofrequency pulses, each lasting a few microseconds, generate sound waves which reflect back and forth between the parallel faces of a crystal specimen of the metal being studied. As the sound wave travels through the crystal specimen of the metal being studied. As the sound wave travels through the metal, it is gradually damped as a result of (at least) four distinct processes: 1) ordinary damping of longitudinal waves as they pass through an isotropic medium; 2) ordinary damping of longitudinal waves as they pass through an isotropic medium; 2) absorption due to the interaction of elastic waves with dislocations in the crystal absorption due to the interactions bestructure; 3) thermoelastic absorption; and 4) absorption due to the interactions between phonons and electrons. The samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the directive of the samples of GaAs and GaSb were oriented in the samples of GaAs and GaSb were oriented in the samples of GaAs and GaSb w

UDC: 534.286

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ACC NR: AP6029535 tions <111>, <110>, and <112>, and both longitudinal and transverse waves we duced. The damping of the sound waves was found to be almost independent of ture, over the range of temperatures considered. However, the damping appear strongly frequency-dependent. The absorption coefficient a depends on the first fas follows: a f. The exponent n, measured experimentally, was found to values between 1.5 and 2.0. Orig. art. has: 4 figures, 1 table, 1 formula.	rs to be requency o take
SUB CODE: 20/ SUBM DATE: 05May65/ ORIG REF: 001/ OTH REF:	007
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"APPROVED FOR RELEASE: Monday, July 31, 2000

CIA-RDP86-00513R000826230

IJP(c) JD/JG EWP(t)/ETI SOURCE CODE: GE/0030/66/017/002/0479/0488 ACC NR AP6033898 AUTHOR: Kravchenko, A. F.; Sardaryan, V. S.

ORG: Institute of Semiconductor Physics, Siberian Division, Academy of Sciences

SSSR, Novosibirsk

TITLE: The bottom structure of the conduction band in GaAs

SOURCE: Physica status solidi, v. 17, no. 2, 1966, 479-488

TOPIC TAGS: magnetoresistance, Hall effect, gallium arsenide, semiconductor physics, semiconductor, semiconductor carrier, conduction band, semiconductor band structure

ABSTRACT: The magnetoresistance and Hall effect were studied for oriented specimens of n-type gallium arsenide with carrier concentrations of 5 x 10^{15} to 1 x 10¹⁸cm⁻³ at temperatures of 78 to 800K. Almost all samples showed anisotropy of the transverse magnetoresistance and nonvanishing longitudinal magnetoresistance. The energy position of the minima and effective mass were estimated from the temperature dependence of the Hall coefficient [AW = 0.12]

Card 1/2

ACC NR. AP6033896 0.36 eV, m; - 1.2 m, m; - 1.95 m, m; - 0.37 m, . A model for the band structure in the vicinity of the conduction band edge was discussed, and was shown to be consistant with experimental data when anisotropy of electron scattering by weak oriented dipoles was taken into account. The authors thanked E. V. Skubnevskii for his assistance in measurements. Orig. art. has: 8 figures, 4 tables, and 13 formulas [Based on authors' abstract] SUB CODE: 20/ SUBM DATE: 30Mar66/ ORIG REF: 012/ OTH REF: 009/ ?

' ACC NR AP6026304 SOURCE CODE: UR/0288/66/000/001/0078/0086 AUTHOR: Kravchenko, A. F.; Sardaryan, V. S. ORG: Institute of Semiconductor Physics, Siberian Department, AN SSSR, Novosibirsk (Institut fiziki poluprovodnikov Sibirskogo Oodeleniya AN SSSR) TITLE: Influence of impurities on the electron energy spectrum in semiconductors SOURCE: AN SSSR. Sibirskoye otdeleniye. Izvestiya. Seriya tekhnicheskikh nauk, no. 1, 1966, 78-86 TOPIC TAGS: electron energy spectrum, semiconductor impurity, electron energy level ABSTRACT: An analytical expression is derived for the density of electron states in a semiconductor, for energy levels of practical interest, in a form convenient for numerical computation. The analysis is developed for a semiconductor containing (of a single type) distributed uniformly over the crystal. The presence of randomly distributed charged particles gives rise in a semiconductor to an additional electrostatic potential that varies from point to point. The field of the charged impurities is characterized by a screening potential proportional to the potential electron energy Card 1/2 621.315.592

ACC NR. AP6026304

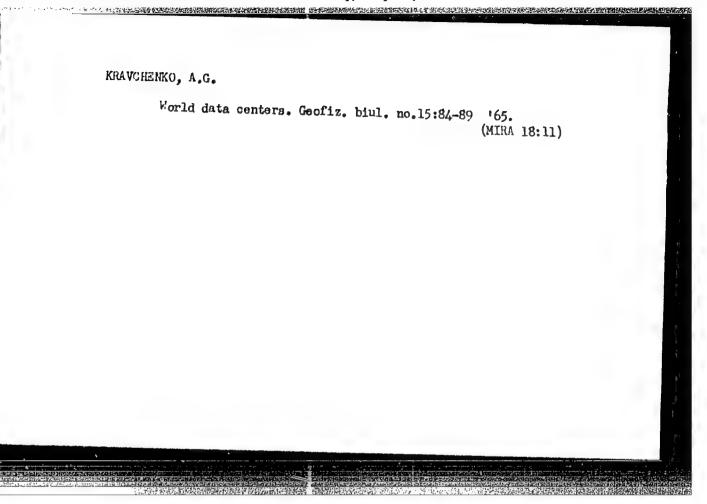
where is the dielectric constant of the semiconductor, and i and j are the electron and impurity numbers, respectively. Based on this model representation, and using the Thomas-Fermi statistical method, the expression for the density of the electron states in the conduction band is obtained in the form

$$\rho(E) = Q \int_{-\infty}^{E} \frac{(E - I)^{1/2} e^{-PI^2}}{(\alpha + \beta I + \gamma I)^{1/2}} dt. \qquad (20).$$

An evaluation of this integral for various electron energies leads to a relation between the density of the electron states in the conduction band and the total electron energy. The specific calculations involved in the analysis are given in appendices. The authors are indebted to I. M. Tsidil'kovskiy, V. V. Serebriakov, N. Ye. Tovmasian, and E. M. Skok for valuable discussions. Orig. art. has: 51 formulas and 1 figure.

SUB CODE: 20/ SUBM DATE: 10Jun65/ ORIG REF: 007/ OTH REF: 008

Card 2/2



ARAVEHENKE, A L. BARTAK, G.Ye.; KRAVOHENKO, A.G. Effect of medinal on exchange of sugar between blood and cerebral cortex. Vop. fiziol. no.7:115-124 154. (MLRA 8:1) 1. Dnepropetrovskiy meditsinskiy institut. (BARBITURATES, effects, barbital sodium on sugar exchange between blood & cerebral cortex) (HEMATOENCEPHALIC BARRIER. eff. of barbital sodium on sugar exchange between blood & cerebral cortex) (BLOOD SUGAR. eff. of barbital sodium on sugar exchange between blood & cerebral cortex) (CEREBRAL CORTEX, physiology, eff. of barbital sodium on sugar exchange between blood & cerebral cortex)

137-58-4-7207

Translation from: Referativnyy zhurnal, Metallurgiya, 1958, Nr 4, p 127 (USSR)

AUTHORS: Fomichev, I.A., Vdovin, F.V., Kravchenko, A.G., Pishchik.

N.S.

TITLE: Manufacture of Tubes From Austenitic lKhl4Nl4V2M (EI-257)

Steel Proizvodstvo trub iz austenitnoy stali 1Kh14N14V2M

(EI-257)]

PERIODICAL: Byul. nauchno-tekhn. inform. Vses. n.-i. trubnyy in-t, 1957, Nr 3, pp 5-16

ABSTRACT: Tubes of 1Kh14N14V2M are designed for use for re-heaters

and manifolds of boilers operating under high and superhigh steam parameters. This steel (S) is a S of the austenitic class and is highly heat-resistant. The effects of temperature and degree of reduction on the plasticity of the S were investigated, and experiments were conducted in rolling the tubes on an automatic 400 mill. Forged hollow and solid blanks with machined surfaces were

employed. Plasticity was determined by torsion testing, by testing for pierceability, and for tension in a single plane (this last method was employed for the first time and makes it possible to determine

Card 1/2 the relationship between the temperature and plasticity, under

137-58-4-7207

Manufacture of Tubes From Austenitic 1Kh14N14V2M (EI-257) Steel

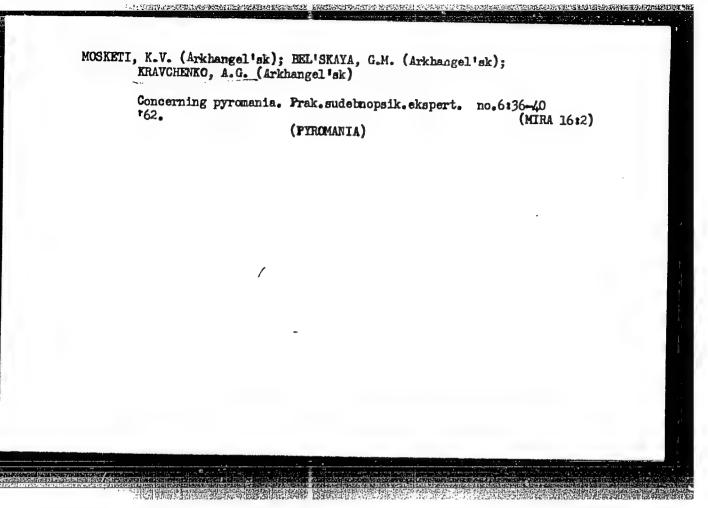
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conditions of stress similar to those of the real stresses existing during piercing, and, consequently, the optimum temperature for the working of the S). The design of the apparatus for testing for plane tension is appended and described. An analysis of the results of the torsion, plane tension, piercing, and microstructure tests is presented. This shows that piercing of the blank should best be performed in the 1200-1225°C temperature interval. The results of tests for pierceability and high-temperature torsion show that as the length of time the metal is held for purposes of heating increases—the plasticity of the S drops. After obtaining the results of laboratory investigation, rolling of tubes of 219x 27 mm dimensions was performed successfully both from hollow and from solid blanks. Solid blanks are recommended as being economically advantageous.

1. Steel tubes--Manufacture 2. Steel tubes--Material

Card 2/2

Card 1/1		Pub. 124 - 16/39	
Authors		Kravchenko, A. G.	
Title	t	Documents on the nomination of N. K. Krupskaya as honorary member of the Acad. of Sc., USSR	
Periodical	ŧ	Vest. AN SSSR 26/2, 92-94, Feb 1956	
Abstract	*	Announcement is made by the Archives of the Academy of Sc., USSR about the preservation of a special protocol dated February 1, 1930, verifying that N. K. Krupskaya (widow of V. I. Lenin) was made an honorary member of the Academy of Sciences, USSR for her great contributions to the development of the Communist ideology. Eleven USSR references (1933-1940).	
Institution	:	••••	,
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ACCESSION NR: AR4018328

8/0137/64/000/001/0038/0038

SOURCE: RZh. Metallurgiya, Abs. 1D237

AUTHOR: Pishchikov, G. P.; Kravchenko, A. G.

TITLE: Making boiler pipe of PZ, 12Kh2MFSR, E1756, E1713, E1695R, and EP17 steels

CITED SOURCE: Sb. Proiz-vo trub. Vy*p. 9.M., Mctallurgizdat, 1963, 13-18

TOPIC TAGS: pipe rolling, steel pipe, steel pipe manufacture, steel plasticity, steel puncture strength, rolling mill operation

TRANSLATION: Tests for warping were conducted on samples 90 and 250 mm in diameter at temperatures of 1,000-1,275 degrees every 50-25 degrees. The plasticity according to the amount of twists was tested to destruction, and the resistance to deformation was studied according to the intensity of twisting. It was determined that the plasticity of 12Kh2MFSR steel up to 1,270 degrees increases continuously (at 1,000 degrees, the number of twists is 22, at 1,250 degrees, 46), steel PZ changes little (at 1,000, the number of twists equals 20, at 1,100 degrees, 22, and at 1,250 degrees, 20). The intensity of twisting for all steel studied diminished proportionately with the increase in temperature. Thus, for three samples of

Cord 1/2

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12Kh2MFSR steel 250 mm in diameter, at 1,000 degrees, the intensity was zero; at 1,100 degrees, 6 kg, and at 1,250 degrees, 1.8 kg. In twisting samples of large diameters, the plasticity of the peripheral zones was higher than that of the central zones. For testing for puncture strength, conical samples were used, which made it possible to have a zone of pressing of 0-14.36. On the basis of the results of tests, schedules for hot rolling of boiler pipes were worked up. Then, pipes measuring 89 x 11 mm were rolled on an automatic "1h0" installation, and pipes measuring 152 x 25, 168 x 26, and 273 x 36 mm were rolled on an automatic "400" installation. Forged faced samples of solid cross-section were used for rolling. Experimental rolling took place normally. The external surface of the pipes was good. The pipes of PZ steel had minor defects 200 mm on their ends. Pipes of EI713, EP17, and EI695R has minor defects on their internal surfaces. Tables are given of the parameters of piercing and set up of the mill, and also the basic industrial parameters for the manufacture of pipes of the above-mentioned types of steel.

SUB CODE: MM, IE

ENCL: OC

Card 2/2

TO MAN THE REPORT OF THE PROPERTY OF THE PROPE

KRAVCHENKO, A.I.

Periodic fluctuations of the intragastric temperature and the periodic motor function of the empty stomach in true gastric achylia. Vrach.delo no.10:91-95 0 '62. (MIRA 15:10)

1. Fakulitetskaya terapevticheskaya klinika (zav. - akademik V.N. Ivanov [decased]) Kiyevskogo meditsinskogo instituta. (STOMACH-SECRETIONS) (PERIODICITY)

CONTROL DESCRIPTION OF THE PROPERTY OF THE PRO

AUTHOR: Kravchenko, A.I. SOV/13U-58-7-29/35

TITLE: According to Increased Obligations (Po povyshennym

obyazatel'stvam)

PERIODICAL: Metallurg, 1958, Nr 7, p 41 (USSR).

ABSTRACT: The author mentions that the personnel of Nr 1 melting shop at the imeni Andreyeva (imeni Andreyev) Works undertook, in honour of the "Day of the Metallurgist" to revise production plans upwards and that his crew (under Stalin prize-winner Zhukov) fulfilled the 1957 production plan to 102.7%, the corresponding figure for the first quarter of 1958 being 106%. He states that his crew are competing with the crew under I.I. Chursinov at the Pervoural'skiy novotrubnyy Works and that the enthusiasm of workers has risen since the introduction of the seven-hour day.

ASSOCIATION: Zavod imeni Andreyeva (imeni Andreyev Works)

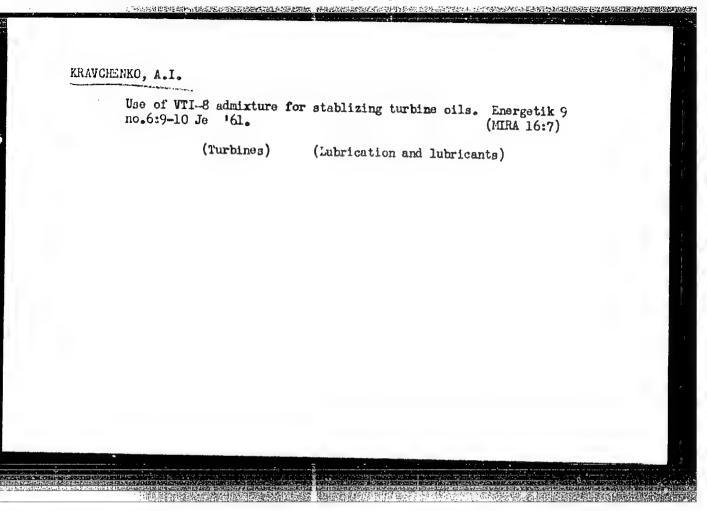
Card 1/1 1. Labor--Performance 2. Labor--USSR 3. Metals--Production

SLUTSKIY, S.S., kand.ekonom.nauk; PILIPCHUK, A.I., nauchnyy sotrudnik; ANTONOV, M.F., kand.tekhn.nauk; MALYARCHUK, G.S., kand.tekhn.nauk. Prinimali uchastiye: MEL'NIKOV, A.A., inzh.; ARSEN'YEVA, A.I., inzh.; TEREKHOVA, Z.S., tekhnik; SIDOROVA, L.N., tekhnik; ISSERLIS, I.I., tekhnik; KRAVCHENKO, A.I., inzh. POSTNIKOV, S.A., inzh., red.; ZHULIN, V.K., otv. za vypusk; POKHLEBKINA, M.I., tekhn.red.

[Efficient distribution of and organization of work at cargo transfer points] Ratsional nos razreshchenie i organizatsiia raboty punktov perevelki. Pod obshchei red. S.S. Slutskogo. Moskva, 1960. 127 p. (HIRA 14:2)

1. Moscow. TSentral'nyy nauchno-issledovatel'skiy institut ekonomiki i ekspluatatsii vodnogo transporta. 2. TSentral'nyy nauchno-issledovatel'skiy institut ekonomiki i ekspluatatsii vodnogo transporta (for Slutakiy, Pilipchuk, Terekhova, Sidorova, Isserlis). 3. Institut komplekenykh transportnykh problem AN SSSR (for Antonov, Malyarchuk, Kravchenko).

(Cargo handling)



KRAVCHENKO, A.1.

Intracutaneous test by means of an autoserum in Botkin's disease. Vrach. delo no.11:86-90 N'63 (MIRA16:12)

1. Kafedra infektsionnykh bolezney Klysyckego meditsinskego instituta.

KRAVCHENKO, A.I.

Intragastric temperature in various diseases. Vrach. delo no.10:36-40 0 '63. (MIRA 17:2)

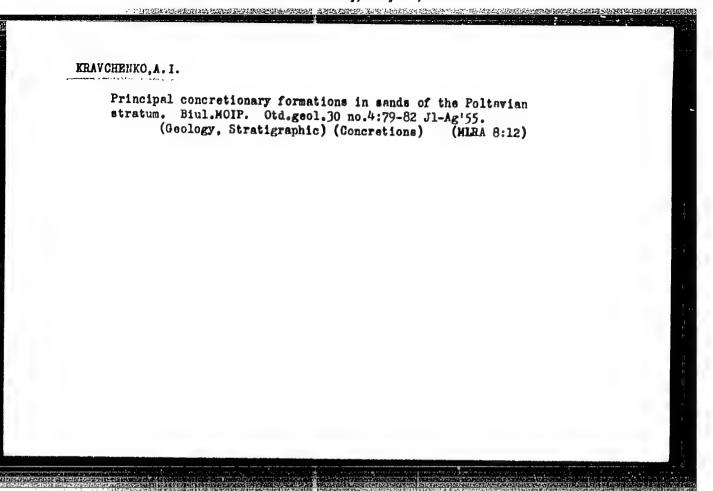
l. Fakulitetskaya terapevticheskaya klinika (zav. - prof. G.I. Burchinskiy) Kiyevskogo meditsinskogo instituta.

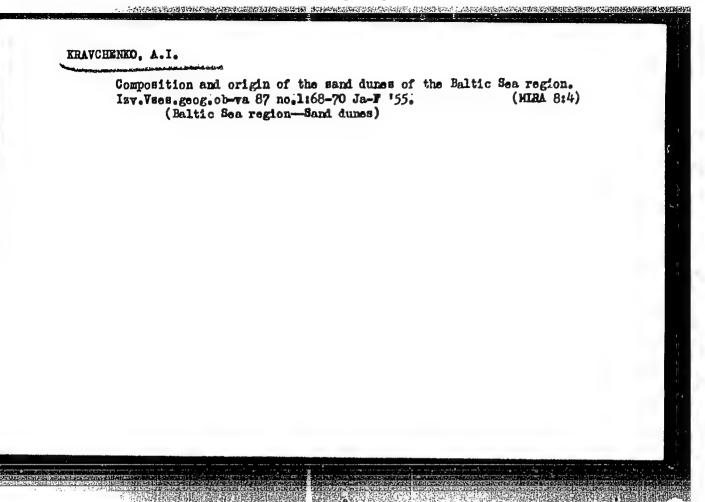
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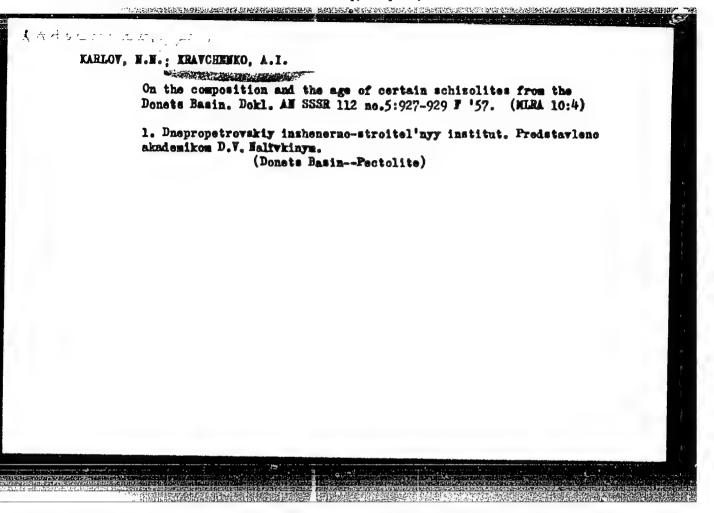
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CIA-RDP86-00513R000826230

TING PROPERTY OF THE PROPERTY KRANCHENKO, A.I. USER/ Geology - Volcanic action Card 1/1 Pub. 86 - 11/37 Authora & Karlov, N. N., and Kravchenko, A. I. Title New deposits of volcanic ashes at Drepropetrovsk Periodical Priroda 44/4, 118 - 119, Apr 1955 Abstract A description is given of volcanic ash deposits at Dniepropetrovsk, which, it is believed, floated in the air for long distances before settling at this point. A study of this rather loose material of relatively recent volcanic action makes possible the determination of the time and intensity of volcanic eruptions in the quarternary and tertiary periods. Illustration; drawing. Institution: Submitted



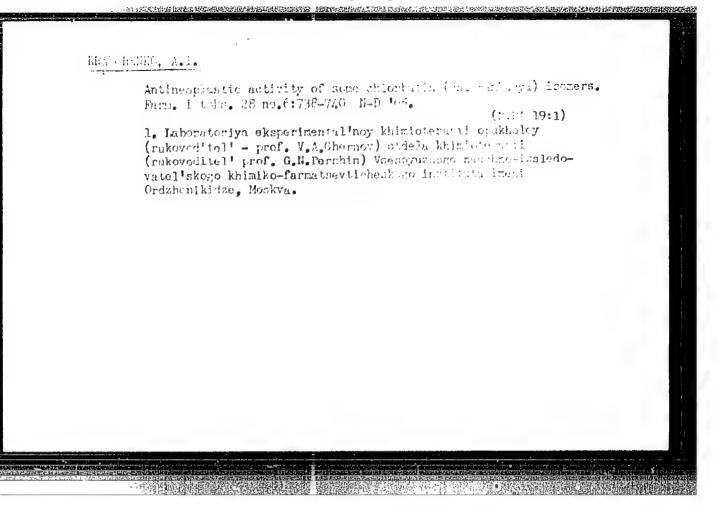




KARLOV, N.N.; KRAVCHENKO, A.I.

Contribution of N.I. Dmitriev to the study of the geology of the Quaternary and the geomorphology of the Ukraine. Biul. Kom. chetv. per. no.24:138-144 '60. (MIRA 16:7)

(Ukraine-Geology)



KRAVCHENKO, A.I. (Moskva, Novo-Gireyevo, 16/45, kv. 44)

Measuring the nucleus size of blastomeres and cells at initial stages of development in Triton taeniatus L. Arkh. anat., gist. i embr. 47 no. 7:22-29 Jl * 64.

1. Imboratoriya eksperimental noy khimioterapii opukholey (rukovoditel - doktor med. nauk V.A. Chernov) Vsesoyuznogo nauchno-issledovatel skogo khimiko-farmatsevticheskogo instituta imeni Ordzhonikidze, Moskva. Submitted April 4, 1963.

CRIGOR'YEV, Te.T., inzhener; KRAVCHENKO, A.I., inzhener.

Utilizing trailing weight of type 2-2 electric locomotives. Vest.
TSNII MPS 15 no.2:22-25 S '56. (MIRA 9:12)

1. Novocherkasskiy elektrovozostroitel'nyy zavod imeni S.M. Budennogo.

(Electric locomotives)

。 1987年,1987年,1987年,1987年,1987年,1987年,1987年,1987年,1987年,1987年,1987年,1987年,1987年,1987年,1987年,1987年,1987年,1987年,1

GRIGOR'YEV, Ye.T., inzh. KRAYCHEMED, A.I., inzh.

Using the adhesien weight of electric lecemotives with eblique traction. Vest. TSMI MPS 17 no.8:23-27 D '58. (MIRA 12:1)

1.Novecherkasskiy elektrovezestreitel'nyy zaved. (Electric lecemetives)

GRIGOR'YEV, Ye.T., inghr; KRAVCHENKO, A.I., ingh.; NESTEROV, S.D., ingh.

Transverse elastic truck couplers for electric locomotives. Yest.
TSNII MPS 18 no.8:21-25 D '59.
(Electric locomotives)

(Electric locomotives)

KRAVCHENKO, A4I., inzh.

Locomotives with a total utilization of the weight on the driving axles. Izv. vys. uchab. zav.; mashinostr. no.3:129-234 60. (MIRA 14:3)

1. Moskovskoye vyssheye tekhnicheskoye uchilishche imeni Baumana. (Locomotives-Dynamics)

KRAVCHENKO, Aleksandr Ignat'yevich

Study of some structural factors of the M60 electric locomotive. Izv. vys. ucheb. zav.; elektromekh. 3 no.3:144-157 '60.

(MIRA 13:10)

l. Nachal'nik laboratorii perspektivnykh razrabotok Novocherkasskogo nauchno-issledovatel'skogo instituta elektrovozostroyeniya.

(Electric locomotives)

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Traction displacements in the carriage of an electric locomotive.

Izv. vys. ucheb. zav.; elektromekh. 3 no.6:112-118 '60. (MIRA 15:5)

1. Nachal'nik laboratorii perspektivnykh razratotok Novocherkasskogo nauchno-issledovatel'skogo instituta elektrovozostroyeniya.

(Electric locomotives)

Investigating the horizontal static interaction of a locomotive and track on curves. Izv.vys.ucheb.zav.; mashinostr. no.7:142-148 '60.

(MIRA 13:11)

1. Novocherkasskiy elektrovomostroitel'nyy zavod.

(Locomotives—Performance)

KRAVCHENKO, A.I.; SITNIK, N.Kh.

Ways of creating main-line electric locomotives on the basis of dimensional series and standardization. Sbor. nauch. trud. EINII 2:72-93 '62. (MIRA 16:8)

(Electric locomotives--Design and construction)

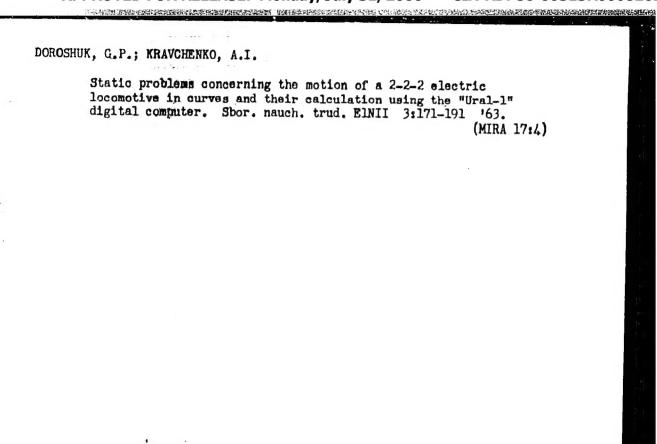
TOTAL STATE OF THE PROPERTY OF THE PERSON OF

KRAYCHENKO, Aleksandr Ignat yevich, inzh.; BRATOLYUBOV, Vsevolod, Borisovich, inzh.

Integral method for evaluating electric traction motors. Izv. vys.ucheb.zav.; elektromekh. 6 no.2:229-236 *63. (MIRA 16:4)

1. Nachal'nik laboratorii perspektivnykh razrabotok Novocherkasskogo nauchno-issledovatel'skogo instituta elektrovozostroyeniya (for Kravchenko). 2. Nachal'nik otdela Mordovskogo nauchno-issledovatel'skogo elektrotekhnicheskogo instituta (for Bratolyubov).

(Electric locomotives) (Electric railway motors)



DOROSHUK, Georgiy Panteleyevich, mladshiy nauchnyy sourudnik; KRAVCHENKO, Aleksandr Ignat yevich, inzh.

Reliability of systems with given statistical characteristics of their quality and applications. Izv. vys. ucheb. zav.; elektromekh. 8 no.4:367-377 165.

1. Vsesoyuznyy nauchno-issledovatel'skiy i proyektno-konstruktorskiy institut elektrovozostroyeniya (for Doroshuk). 2. Nachal'nik laboratorii perspektivnykh razrabotok Vsesoyuznogo nauchno-issledovatel'skogo i proyektno-konstruktorskogo instituta elektrovozostroyeniya (for Kravchenko).

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KRAVCHENKO, Aleksandr Ignat'yevich, inzh.; ZHAVCHENKO, Marine Ignat'yevic, ordinator

Use of a digital computer in solving a problem on the cognition of a logical image described by discrete information. Izv. vys. ucheb. zav.; elektromekh. 8 no.4:472-473 '65.

1. Nachal'nik laboratorii perspektivnykh razrabotok Vsesoyuznogo nauchno-issledovatel'skogo i proyektno-konstruktorskogo instituta neuchno-issledovatel'skogo i proyektno-konstruktorskogo instituta elektrovozostroyeniya (for Kravchenko, A.I.). 2. Klinika nervnykh bolezney i neyrokhirurgii Rostovskogo meditsinskogo instituta (for Kravchenko, M.I.).